

30mA 40V Low VF(For Glass Seal)

Chip Information

Chip Size	0.30 x 0.30mm
Pad Size	0.12 x 0.12mm
Chip Quantity	122959 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ag Bump(For Glass Seal)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	30	mA	
Peak Forward Surge Current	IFSM	0.2	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Test Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.370	0.360	0.320	V	IF=1mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.5	0.15	0.06	uA	VR=25V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV1	42	44	55	V	IR=20uA
	BV2	42	44	55	V	IR=100uA
	deltaBV	2.5	2		V	BV2-BV1
Junction Capacitance	Cj			2	pF	V=1V,f=1MHz
Reverse Recovery Time	trr			0.8	nS	IF=IR=10mA irr=1mA

Ordering Information

Chip Type	Chip Thickness	Back Metal
YHK03A	150 +/- 20um	Ti-Ni-Ag(For Glass Seal)

Note:
Designed For RB721Q